＊ 陳始明教授

所有發表期刊論文

PUBLICATION LIST

BOOKS

1. C. M. Tan, W. Li, Z. Gan, and Y. Hou. *Applications of finite element methods for reliability studies on ULSI Interconnections*. UK: Springer Verlag, 2011.
2. C. M. Tan. *Electromigration in ULSI Interconnections*. New York: World Scientific, 2010.
3. C. M. Tan. *Simulated Annealing.* Vienna, Austria: IN-TECH Publishing, 2008.
4. C. M. Tan and F. He. *Electromigration Modeling at Circuit Layout Level.* SpringerBrief on Reliability, 2013.

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2. C. M. Tan and N. Raghavan. "Simulated Annealing for Mixture Distribution Analysis and its Applications to Reliability Testing" in *Simulated Annealing*. Vienna, Austria: IN-TECH Publishing, 2008, pp.227-256.
3. Tan Cher Ming and Hou Yuejin. "Changing Reliability Physics of Interconnect from Micro- to Nanotechnology", in *Ceramic Integration and Joining Technologies: From Macro to Nanoscale,* John Wiley, 2010
4. Cher Ming Tan, "Component Level Reliability: Physical models and testing regulations" in "Handbook of Advanced Lighting Technology", Springer-Verlag GmbH, Germany, 2014.

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